BLC8G27LS-160AV

Power LDMOS transistor

Rev. 2 — 3 June 2014 | Product data sheet

1. Product profile

1.1 General description

160 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2496 MHz to 2690 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in the Doherty demo board.

Test signal	f	V_{DS}	$P_{L(AV)}$	G_p	η_D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2496 to 2690	28	31.6	14.5	43	–30 [1]

[1] Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

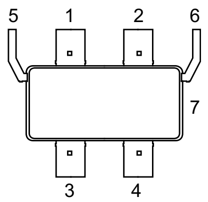
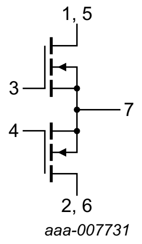
- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

1.3 Applications

- RF power amplifier for W-CDMA base stations and multi carrier applications in the 2496 MHz to 2690 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1 (main)		
2	drain2 (peak)		
3	gate1 (main)		
4	gate2 (peak)		
5	video decoupling (main)		
6	video decoupling (peak)		
7	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLC8G27LS-160AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		−0.5	+13	V
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
Main device				
$R_{th(j-case)}$	thermal resistance from junction to case	T_{case} = 80 °C; V_{DS} = 28 V; I_{Dq} = 490 mA		
		P_L = 32 W	0.509	K/W
		P_L = 100 W	0.363	K/W

Table 5. Thermal characteristics *...continued*

Symbol	Parameter	Conditions	Typ	Unit
Peak device				
$R_{th(j-case)}$	thermal resistance from junction to case	T_{case} = 80 °C; V_{DS} = 28 V; I_{Dq} = 490 mA		
		P_L = 32 W	0.069	K/W
		P_L = 100 W	0.284	K/W

6. Characteristics

Table 6. DC characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Main device						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.9 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 90 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 300 mA	1.6	2.0	2.4	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	μA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	17	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 90 mA	-	0.78	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 3.15 A	-	174	260	mΩ
Peak device						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 1.1 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 110 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 600 mA	1.6	2.0	2.4	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	μA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	20	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 110 mA	-	0.97	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 3.85 A	-	145	215	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 - 64 DPCH; f_1 = 2496 MHz; f_2 = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.70 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)}$ = 31.6 W	13.3	14.3	-	dB
RL_{in}	input return loss	$P_{L(AV)}$ = 31.6 W	-	−13	−6	dB
η_D	drain efficiency	$P_{L(AV)}$ = 31.6 W	36	41	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 31.6 W	-	−30	−25	dBc

Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 - 64 DPCH; f = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.7 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	$P_{L(AV)}$ = 63 W	3.75	4.7	-	dB
$P_{L(M)}$	peak output power		146	170	-	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC8G27LS-160AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.7 V; P_L = 120 W (CW); f = 2496 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 570 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [2]	G_p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum power load					
2496	2 – j6.9	1.6 – j7.6	109	56	13.7
2600	3 – j7	1.5 – j8.1	107	52.8	13.9
2690	5.2 – j8.7	1.5 – j8.1	103	54.6	14.8
Maximum drain efficiency load					
2496	2 – j6.9	2.6 – j6.6	89	64	15.6
2600	3 – j7	2.6 – j6.6	79	63	16.5
2690	5.2 – j8.7	2.1 – j7.1	81	61	16.7

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 680 mA (peak); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [2]	G_p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum power load					
2496	2 – j6.9	3.3 – j8.3	128	56.9	15.2
2600	3 – j7	3.3 – j8.3	118	57	15.6
2690	5.2 – j8.7	4 – j10	120	52.5	15.6

Table 10. Typical impedance of peak device *...continued*

Measured load-pull data of peak device; I_{Dq} = 680 mA (peak); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [2]	G_p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum drain efficiency load					
2496	2 – j6.9	3.5 – j5.8	94	63	17
2600	3 – j7	3.5 – j5.8	83	60	17.7
2690	5.2 – j8.7	3.3 – j7.7	97	59	17.4

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

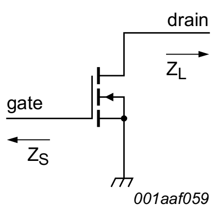


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load

Measured load-pull data of main device; I_{Dq} = 570 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [3]	G_p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2496	2 – j6.9	2.7 – j7.1	49.7	40	18.5
2600	3 – j7	2.7 – j7.1	49.4	41	19.3
2690	5.2 – j8.7	2.7 – j7.1	49.1	42	19.5

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

[3] at $P_{L(AV)}$ = 44.5 dBm.

Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device; I_{Dq} = 750 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [3]	G_p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2496	2 – j6.9	2.9 – j4.5	44.56	48	19.8
2600	3 – j7	2.9 – j4.5	44.44	53	20.9
2690	5.2 – j8.7	3 – j4.9	44.5	50.3	20.8

[1] Z_S and Z_L defined in Figure 1.

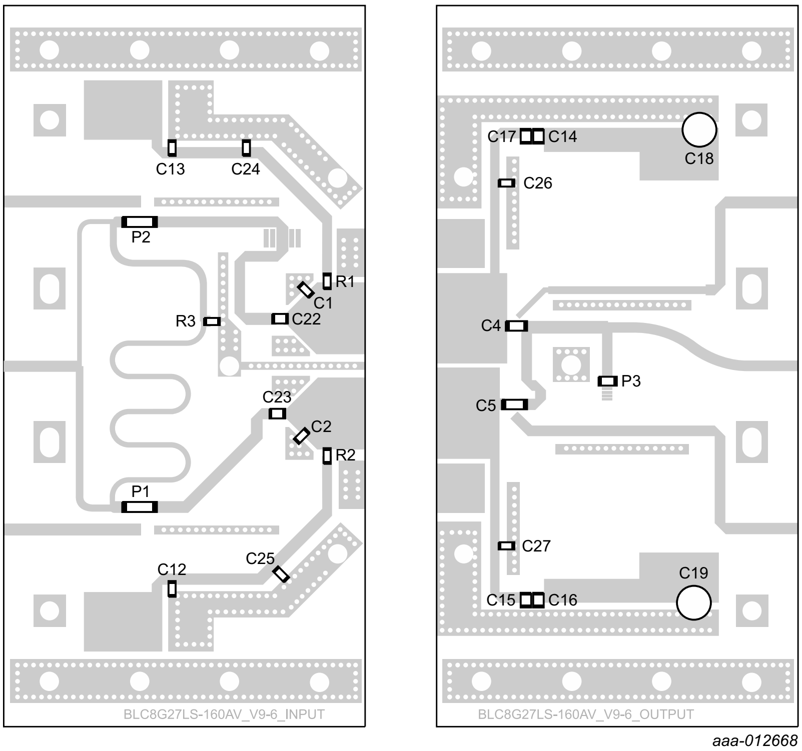
[2] at 3 dB gain compression.

[3] at $P_{L(AV)}$ = 44.5 dBm.

7.4 VBW in Doherty operation

The BLC8G27LS-160AV shows 130 MHz (typical) video bandwidth in Doherty demo board in 2600 MHz at V_{DS} = 28 V; I_{Dq} = 250 mA and $V_{GS(amp)peak}$ = 0.8 V.

7.5 Test circuit



Printed-Circuit Board (PCB): Rogers RO4350B; ε_r = 3.5; thickness = 0.508 mm; thickness copper plating = 35 μm.

See Table 13 for a list of components.

Fig 2. Component layout

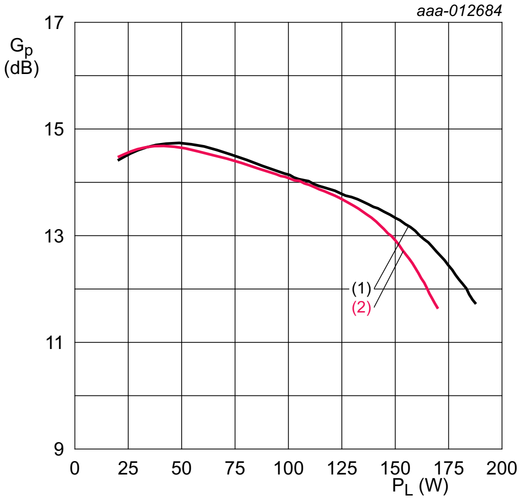
Table 13. List of components

See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	0.3 pF	ATC 600F
C4	multilayer ceramic chip capacitor	3.3 pF	ATC 600F
C5, C22, C23, C24, C25, C26, C27	multilayer ceramic chip capacitor	10 pF	ATC 600F
C12, C13	multilayer ceramic chip capacitor	1 μF	Murata, SMD 1206
C14, C15, C16, C17	multilayer ceramic chip capacitor	10 μF	Murata, SMD 1206
C18, C19	electrolytic capacitor	2200 μF, 63 V	BCcomponents
P1, P2, P3	copper foil strip	-	needed for tuning
R1, R2	resistor	5.1 Ω	SMD 0805

7.6 Graphical data

7.6.1 Pulsed CW

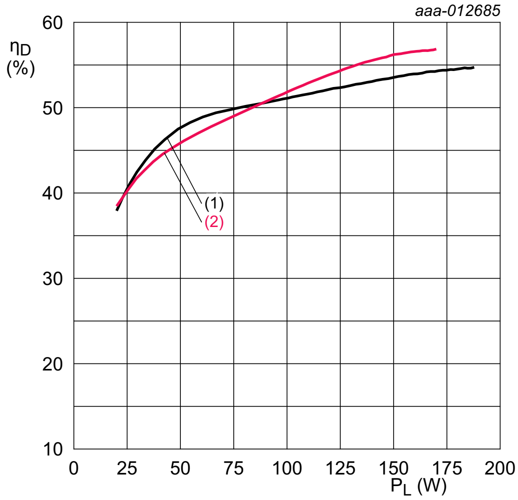


V_{DS} = 28 V; I_{Dq} = 250 mA (main device);
$V_{GS(amp)peak}$ = 0.65 V; t_p = 100 μs; δ = 10 %.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 3. Power gain as a function of output power; typical values

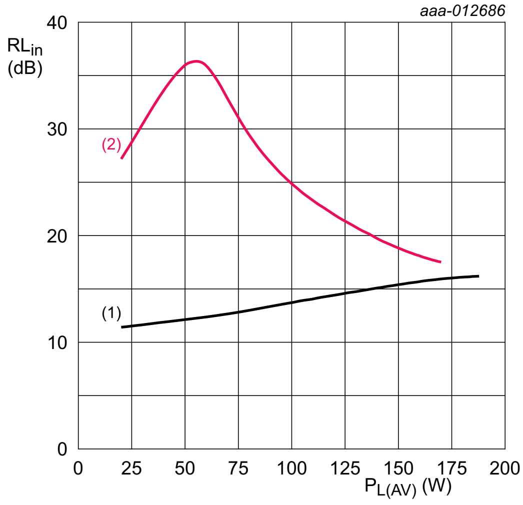


V_{DS} = 28 V; I_{Dq} = 250 mA (main device);
$V_{GS(amp)peak}$ = 0.65 V; t_p = 100 μs; δ = 10 %.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 4. Drain efficiency as a function of output power; typical values



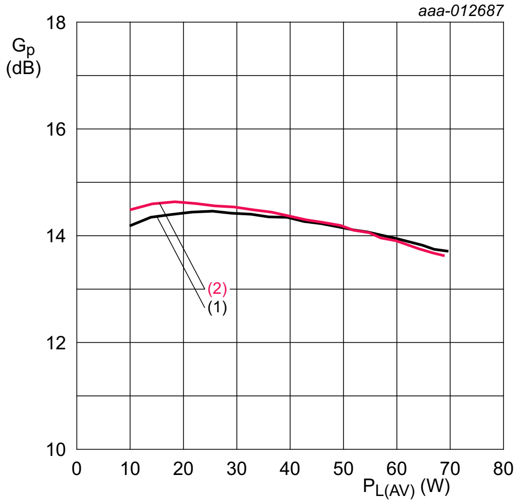
V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V; t_p = 100 μs; δ = 10 %.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 5. Input return loss as a function of average output power; typical values

7.6.2 1-Carrier W-CDMA

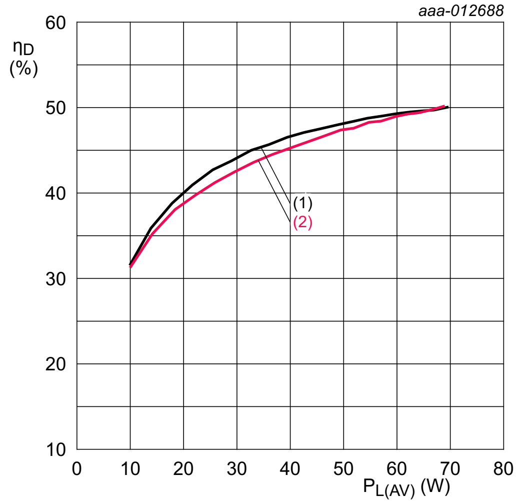


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 6. Power gain as a function of average output power; typical values

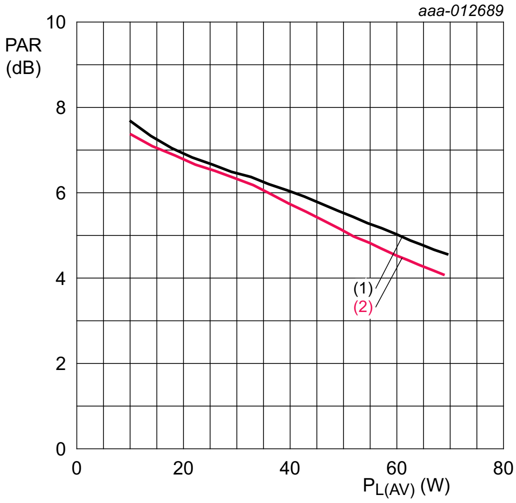


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 7. Drain efficiency as a function of average output power; typical values

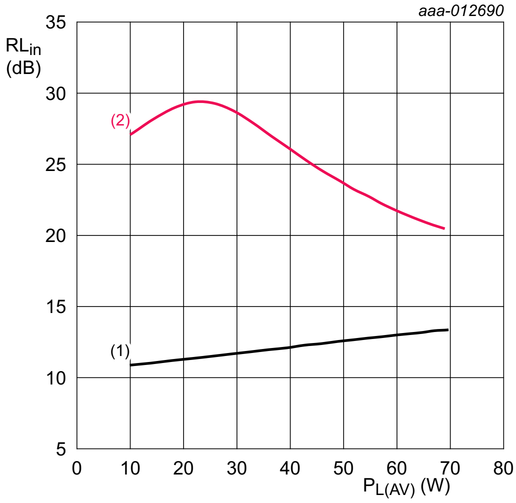


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 8. Peak-to-average power ratio as a function of average output power; typical values

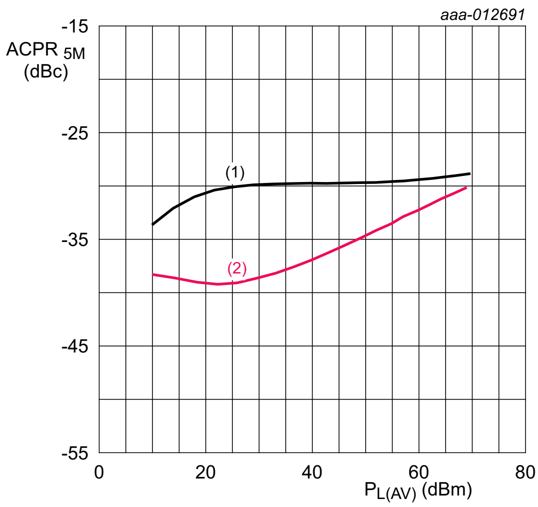


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 9. Input return loss as a function of average output power; typical values

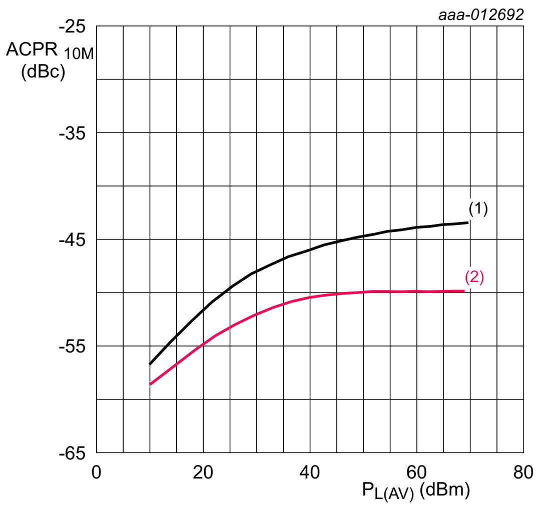


V_{DS} = 28 V; I_{Dq} = 250 mA (main device);
$V_{GS(amp)peak}$ = 0.65 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 10. Adjacent channel power ratio (5 MHz) as a function of average output power; typical values



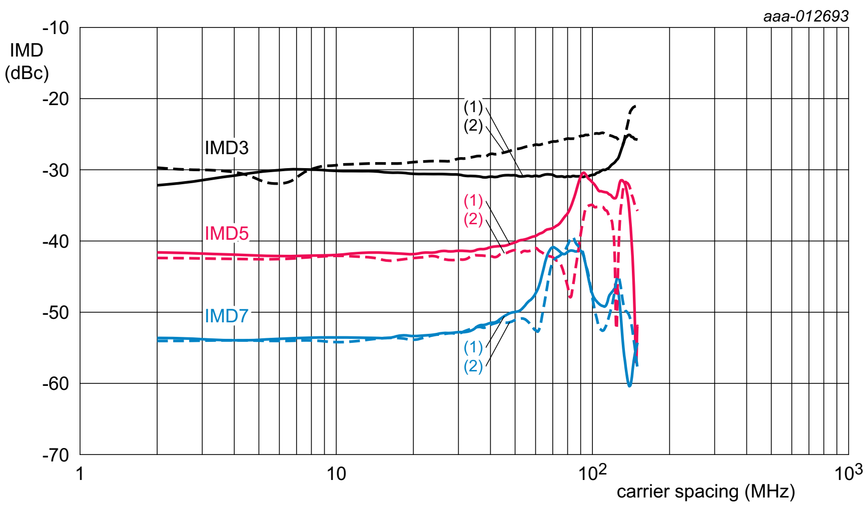
V_{DS} = 28 V; I_{Dq} = 250 mA (main device);
$V_{GS(amp)peak}$ = 0.65 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 11. Adjacent channel power ratio (10 MHz) as a function of average output power; typical values

7.6.3 2-Tone VBW



V_{DS} = 28 V; I_{Dq} = 250 mA; f_c = 2600 MHz.

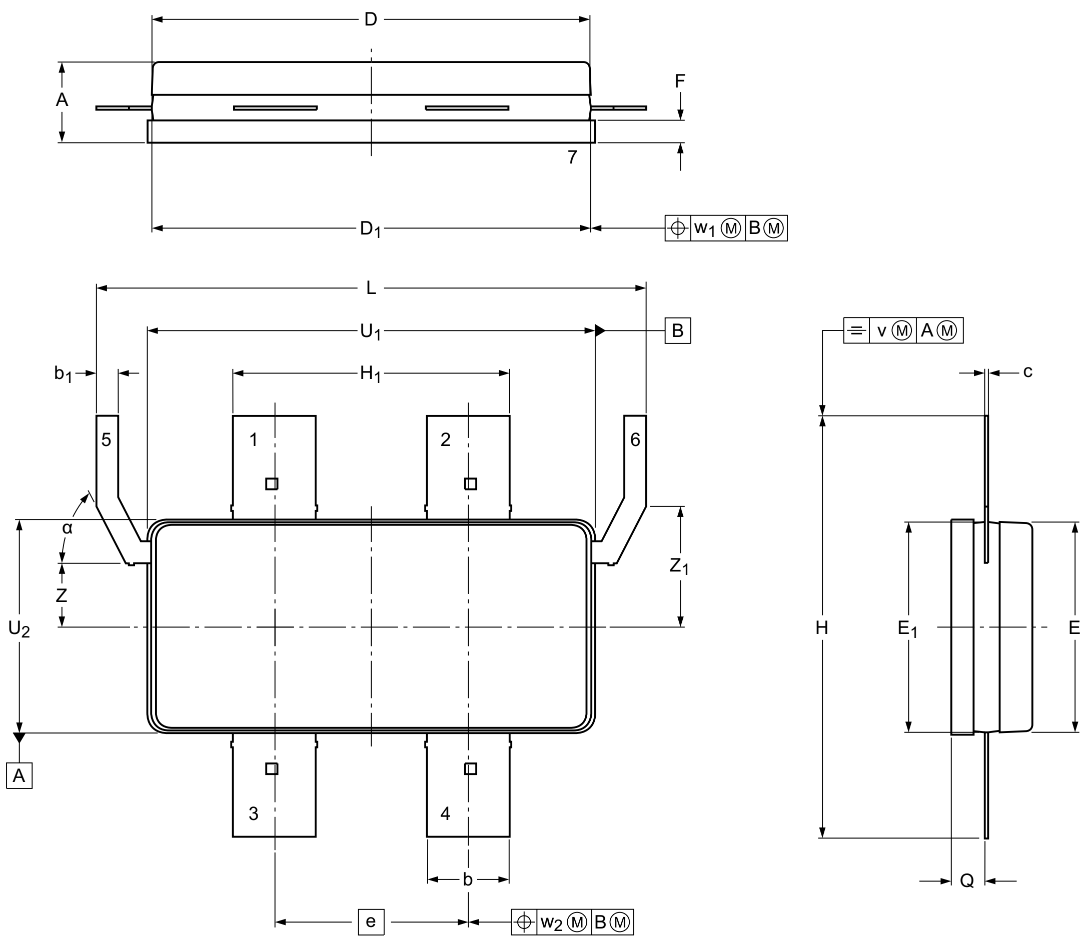
(1) IMD low

(2) IMD high

Fig 12. VBW capability in Doherty demo board

8. Package outline

Air cavity plastic earless flanged package; 6 leads **SOT1275-1**



v	w_1	w_2
0.5	0.5	0.5

0 5 10 mm
scale

Dimensions (mm dimensions are derived from the original inch dimensions)

Unit		A	b	b_1	c	D	D_1	E	E_1	e	F	H	H_1	L	Q	U_1	U_2	Z	Z_1	α
mm	max	4.01	3.94	1.14	0.178	20.42	20.37	9.80	9.75		1.14	19.53	12.80	25.40	1.68	20.70	9.91	3.67	5.79	65°
	nom									8.89										
	min	3.40	3.68	0.89	0.127	20.12	20.17	9.50	9.55		0.94	19.33	12.60	25.20	1.45	20.50	9.70	3.17	5.29	61°

sot1275-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1275-1						~~13-10-08~~ 14-01-13

Fig 13. Package outline SOT1275-1

9. Handling information

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 14. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Moulded Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G27LS-160AV v.2	20140603	Product data sheet	-	BLC8G27LS-160AV v.1
Modifications:	• Table 1 on page 1: Table has been updated • Table 3 on page 2: Table has been updated • Table 5 on page 2: Table has been updated • Table 6 on page 3: Table has been added • Table 7 on page 3: Table has been added • Table 8 on page 4: Table has been added • Section 7.1 on page 4: Section has been updated • Section 7.2 on page 4: Section has been added • Section 7.3 on page 5: Section has been added • Section 7.4 on page 6: Section has been added • Section 7.5 on page 6: Section has been added • Section 7.6 on page 7: Section has been added • Figure 13 on page 10: Package Outline drawing has been changed			
BLC8G27LS-160AV v.1	20130523	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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14. Contents

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